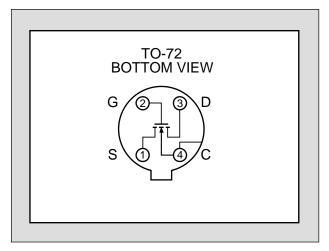


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FEATURES						
DIRECT REPLACEMENT FOR INTERSIL 2N4351						
IGH DRAIN CURRENT I _D = 100mA						
HIGH GAIN $g_{fs} = 1000 \mu S$						
ABSOLUTE MAXIMUM RATINGS ¹						
@ 25 °C (unless otherwise stated)						
Maximum Temperatures						
Storage Temperature	-65 to +200 °C					
Operating Junction Temperature	-55 to +150 °C					
Maximum Power Dissipation						
Continuous Power Dissipation	375mW					
Maximum Current						
Drain to Source	ource 100mA					
Maximum Voltages						
Drain to Body	25V					
Drain to Source	25V					
Peak Gate to Source ² ±125V						

2N4351

N-CHANNEL MOSFET ENHANCEMENT MODE



^{*} Body tied to Case.

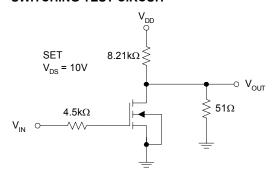
ELECTRICAL CHARACTERISTICS @ 25 °C (unless otherwise stated) (V_{SB} = 0V unless otherwise stated)

SYMBOL	CHARACTERISTIC	MIN	TYP	MAX	UNITS	CONDITIONS
BV _{DSS}	Drain to Source Breakdown Voltage	25				$I_D = 10 \mu A, V_{GS} = 0 V$
$V_{DS(on)}$	Drain to Source "On" Voltage			1	V	$I_D = 2mA$, $V_{GS} = 10V$
$V_{GS(th)}$	Gate to Source Threshold Voltage	1		5		$V_{DS} = 10V, I_{D} = 10\mu A$
I _{GSS}	Gate Leakage Current			10	pА	$V_{GS} = \pm 30V$, $V_{DS} = 0V$
I _{DSS}	Drain Leakage Current "Off"			10	nA	$V_{DS} = 10V$, $V_{GS} = 0V$
$I_{D(on)}$	Drain Current "On"	3			mA	V _{GS} = 10V, V _{DS} = 10V
9 fs	Forward Transconductance	1000			μS	$V_{DS} = 10V, I_{D} = 2mA, f = 1MHz$
r _{DS(on)}	Drain to Source "On" Resistance			300	Ω	$V_{GS} = 10V, I_D = 0A, f = 1kHz$
C _{rss}	Reverse Transfer Capacitance			1.3		$V_{DS} = 0V, V_{GS} = 0V, f = 140kHz$
C_{iss}	Input Capacitance			5.0	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 140kHz$
$C_{\sf db}$	Drain to Body Capacitance		·	5.0		V _{DB} = 10V, <i>f</i> = 140kHz

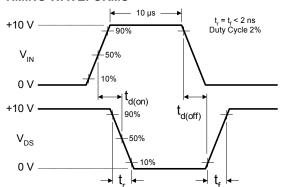
SWITCHING CHARACTERISTICS

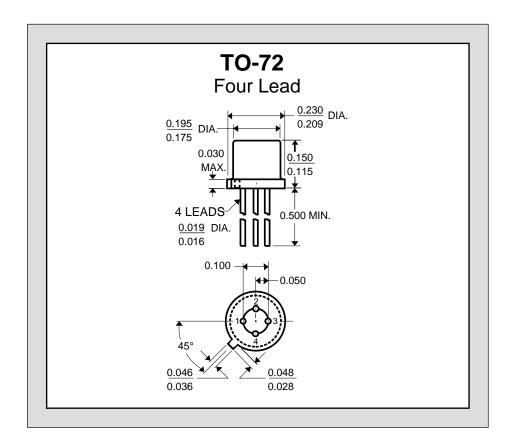
SYMBOL	CHARACTERISTIC	MAX	UNITS			
t _{d(on)}	Turn On Delay Time	45				
t _r	Turn On Rise Time	65	20			
t _{d(off)}	Turn Off Delay Time	60	ns			
t _f	Turn Off Fall Time	100				

SWITCHING TEST CIRCUIT



TIMING WAVEFORMS





- Absolute maximum ratings are limiting values above which serviceability may be impaired.
- Device must not be tested at ±125V more than once or longer than 300ms.

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